

FINAL PRODUCT/PROCESS CHANGE NOTIFICATION

Generic Copy

11-Apr-2006

SUBJECT: ON Semiconductor Final Product/Process Change Notification #15507

TITLE: Qualification of OSPI for Assembly/Test of 8/14/16 Lead SOIC Narrow Packages

EFFECTIVE DATE: 11-Jun-2006

AFFECTED CHANGE CATEGORY(S): ON Semiconductor Assembly and Test

AFFECTED PRODUCT DIVISION(S): Analog Power Management

ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or Matt Kas <fft7yg@onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Alan Garlingtoncpr180@onsemi.com

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 60 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact your local ON Semiconductor Sales Office.

DESCRIPTION AND PURPOSE:

Final Process Change Notice to notify customers of the capacity expansion of the ON Semiconductor assembly/test location at Carmona, Philippines (OSPI) for 8/14/16 lead narrow SOIC packages. The devices listed on this FPCN have historically been assembled/tested at the ASE assembly/test facility located in Chung Li, Taiwan. At the expiration of this Initial PCN and subsequent Final PCN, these devices may be processed at either location. The ON Semiconductor facility at Carmona, Philippines is fully qualified and has been producing the SOIC narrow body products for many years. The capacity expansion will involve duplication of the existing equipment set currently in production.

Please refer to Initial PCN notice number 15335 and Update Notice 15453 which are both related to this change.

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RELIABILITY DATA SUMMARY:

Standard equipment set certification procedures will be followed prior to being placed into production.

Reliability qualification is through qualification by similarity with existing production.

ELECTRICAL CHARACTERISTIC SUMMARY:

Electrical performance will not change. Device parameters will continue to meet all data sheet specifications, and reliability will continue to meet or exceed ON Semiconductor standards.

CHANGED PART IDENTIFICATION:

Assembly lot traceability codes can be used to determine the assembly factory

AFFECTED DEVICE LIST:

PARTS

MC1403D

MC1403DR2

MC26LS30D

MC26LS30DR2

MC33232D

MC33232DG

MC33232DR2

MC33232DR2G

MC33260D

MC33260DG

MC33260DR2

MC33260DR2G

MC33364D

MC33364D1

MC33364D1R2

MC33364D2

MC33364D2R2

MC33364DG

MC33364DR2

MC33364DR2G

MC33368D

MC33368DG

MC33368DR2

MC33368DR2G

MC33567D-1R2G

NCP1603D100R2

SC33262DR2

SC33262DR2G

SC78L12ABDR2

UAA2016AD

UAA2016D



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Select Report Type Select Qualification Type

Date: October 23, 2001 PCN: 11634

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Reliability Engineer Reliability Manager

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1) Introduction:

This reliability study was used to qualify the ON Semiconductor Carmona, Philippines assembly site (OSPI) for Pure tin(Sn) metal finish to be applied to it's existing SOIC packages using SOIC 16, and 8 leads lead package as qualification vehicle.

2) Device Descriptions:

Qual Lot ID1804Wafer Fab SiteDeviceMC78L05ACDAssembly SiteOSPI CARMONALine SourceTEMC78L05DFinal Test SiteOSPI CARMONA

Parent Tech Linear Voltage Regulator Reliability Lab OSPI CARMONA

Technology Bipolar Max. Current 40mA Max. Voltage 30v

Package SOIC 8 Die Size 1.17 x 1.22mm Flag Size 1.778 x 2.286mm

Polarity

Qual Lot ID 1805 Wafer Fab Site

Device MC1413D Assembly Site OSPI CARMONA
Line Source D100P7KQ Final Test Site OSPI CARMONA
Parent Tech Darlington Transistor Reliability Lab OSPI CARMONA

Technology Bipolar Max. Current 500mA Max. Voltage 30v

Package SOIC 16 **Die Size** 1.727 x 2.515mm **Flag Size** 2.286 x 3.302mm

Polarity

Related Qualification Report(s):

The SOIC 16, and 8 lead packages are chosen as qual vehicles for pure tin plating of SOIC packages. SOIC 14 leads, ar intermediate leadcount, is qualified by similarity



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3) Qualification Results Analysis:

Environmental Stress Test Results Summary: ZERO REJECTS achieved for the following tests: Preconditioning: Mositure Level 1 (MSL1) HTOL: Ta = +145°C, Tj = +150°C to 504 Hrs

HAST-PC: Ta = +130°C, RH = 85%, P = 18 PSIG to 96 Hrs

TC-PC: Ta = -65°C to +150°C to 1000 cycles

HTB: $Ta = 175^{\circ}C$ to 504 Hr

AC-PC: Ta = +121°C, RH = 100%, P = 15 PSIG to 96 Hrs

The complete test results are listed in the Test Summary section. The **bold** lettering in the Test Summary interval column indicates qualification point. The hours or cycles after the bold lettering are extended readout points.

4) Conclusion:

The reliability test results reported herein qualify the pure Sn plating for use in SOIC 8, 14, and 16 lead packages at ON Semiconductor Carmona, Philippines (OSPI). The pure Sn plating for these products meets or exceeds ON Semiconductor's requirements for Product Reliability as set forth in "Product Reliability Qualification Process," specification 12MSB17722C Issue G.



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5) Test Description & Condition:

Auto-PC	Autoclave - PC	AUTOCLAVE + MOISTURE LEVEL PRECONDITIONING
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Autoclave is an environmental test which measures device resistance to moisture

penetration and the resultant effects of galvanic corrosion. Autoclave is a highly accelerated

and destructive test.

Typical Test Conditions: TA = 121°C, rh = 100%, p = 15 psig

Common Failure Modes: Parametric shifts, high leakage and/or catastrophic

Common Failure Mechanisms: Die corrosion or contaminants such as foreign material on

or within the package materials. Poor package sealing

HAST-PC Highly Accelerated

Stress Test - PC

HIGHLY ACCELERATED STRESS TEST + MOISTURE LEVEL PRECONDITIONING

HAST uses a pressurized environment to produce extremely severe temperature, humidity and bias conditions. HAST accelerates the same failure mechanisms as High Humidity High

Temperature Bias.

Test Conditions: TA = 131° C, rh = 85%, p = 18 psig

Common Failure Modes: Parametric shifts, high leakage and/or catastrophic

Common Failure Mechanisms: Die corrosion or contaminants such as foreign material on

or within the package materials. Poor package sealing

HTB **High Temperature**

Bake

HIGH TEMPERATURE BAKE

High temperature storage life testing is performed to accelerate failure mechanisms which

are thermally activated through the application of extreme temperatures.

Test Conditions: TA = 175°C

Common Failure Modes: Parametric shifts in leakage and gain Common Failure Mechanisms: Bulk die and diffusion defects

High Temperature **HTOL**

Operating Life

HIGH TEMPERATURE OPERATING LIFE

The purpose of this test is to evaluate the bulk stability of the die and to generate defects resulting from manufacturing aberrations that are manifested as time and stress-dependent

failures.

Test Conditions: TA = 145°C

Common Failure Modes: Parametric shifts and catastrophic

Common Failure Mechanisms: Foreign material, crack die, bulk die, metallization, wire and

die bond defects

TC-PC **Temperature**

Cycling - PC

TEMPERATURE CYCLING + MOISTURE LEVEL PRECONDITIONING

The purpose of this test is to evaluate the ability of the device to withstand both exposure to extreme temperatures and transitions between temperature extremes. This testing will also

expose excessive thermal mismatch between materials.

Test Conditions: TA = -65°C to 150°C, air to air

Common Failure Modes: Parametric shifts and catastrophic

Common Failure Mechanisms: Wire bond, cracked or lifted die and package failure

MSL-1 Moisture Level 1 MOISTURE LEVEL PRECONDITIONING

These tests are performed to simulate the board mounting process where parts are subjected to a high temperature for a short duration. These tests detect mold compound delamination from the die and leadframe. The failure mechanisms are corrosion, fractured

wirebonds and passivation cracks.

10TC + 24Hr Bake@125°C + 168Hr 85/85 + 3 IR@260°C + 1X Flux Immersion + DI Rinse

Test Summary

Test Name	Test Conditions & Bias	Lot ID	Interva	33	ĸej	Comment
Auto-PC	TA = +121°C, RH = 100%, PSIG = 15	1804A		77	0	



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			77	0	
			77	0	
		1804B	77	0	
			77	0	
			77	0	
		1804C	77	0	
			77	0	
			77	0	
		1805A	77	0	
			77	0	
			77	0	
		1805B	77	0	
			77	0	
			77	0	
		1805C	77	0	
			77	0	
			77	0	
НТВ	$TA = 175^{\circ}C$	1804A	77	0	
			77	0	
			77	0	
		1804B	77	0	
			77	0	
		10010	77	0	
		1804C	77	0	
			77	0	
		1	77	0	

Test Name	Test Conditions & Bias	Lot ID	Interval	SS	Rej	Comment	
<u> </u>							

Test Name

Test Conditions & Bias



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		1805A	0 hour	77	0	
			504 hours	77	0	
			1008 hours	77	0	
		1805B	0 hour	77	0	
			504 hours	77	0	
			1008 hours	77	0	
		1805C	0 hour	77	0	
			504 hours	77	0	
			1008 hours	77	0	
HTOL	T _A =145°C, V _{CC} =40V	1804A	0 hour	77	0	
			250 hours	77	0	
			504 hours	77	0	
		1804B	0 hour	77	0	
			250 hours	77	0	
			504 hours	77	0	
		1804C	0 hour	77	0	
			250 hours	77	0	
			504 hours	77	0	
		1805A	0 hour	77	0	
			250 hours	77	0	
			504 hours	77	0	
		1805B	0 hour	77	0	
			250 hours	77	0	
			504 hours	77	0	
		1805C	0 hour	77	0	
			250 hours	77	0	
			504 hours	77	0	

SS

Interval

Lot ID

Rej Comment

Test Name

Test Conditions & Bias



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HAST - PC	TA - +131°C, RH - 85%, FSIG - 18, VCC-40V	1004A	0 hour	77	0	
			96 hours	77	0	
			192 hours	77	0	
		1804B	0 hour	77	0	
			96 hours	77	0	
			192 hours	77	0	
		1804C	0 hour	77	0	
			96 hours	77	0	
			192 hours	77	0	
		1805A	0 hour	77	0	
			96 hours	77	0	
			192 hours	77	0	
		1805B	0 hour	77	0	
			96 hours	77	0	
			192 hours	77	0	
		1805C	0 hour	77	0	
			96 hours	77	0	
			192 hours	77	0	
TC - PC	Air to Air; -65°C to +150°C	1804A	0 cycles	77	0	
			500 cycles	77	0	
			1000 cycles	77	0	
		1804B	0 cycles	77	0	
			500 cycles	77	0	
			1000 cycles	77	0	
		1804C	0 cycles	77	0	
			500 cycles	77	0	
			1000 cycles	77	0	

OSPI Reliability Engineering Services

SS

Interval

Lot ID

Rej Comment



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		1805A	0 cycles	77	0	
			500 cycles	77	0	
			1000 cycles	77	0	
		1805B	0 cycles	77	0	
			500 cycles	77	0	
			1000 cycles	77	0	
		1805C	0 cycles	77	0	
			500 cycles	77	0	
			1000 cycles	77	0	
MSL1-260	10TC + 24Hr Bake@125°C + 168Hr 85/85 + 3x	1804A	0 hour	231	0	
	IR@260°C + 1X Flux Immersion + DI Rinse + Visual		Readout	231	0	
		1804B	0 hour	231	0	
			Readout	231	0	
		1804C	0 hour	231	0	
			Readout	231	0	
		1805A	0 hour	231	0	
			Readout	231	0	
		1805B	0 hour	231	0	
			Readout	231	0	
		1805C	0 hour	231	0	
			Readout	231	0	



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